

Sa Hoang Huynh

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Effects of In-Situ Plasma-Enhanced Atomic Layer Deposition Treatment on the Performance of HfO ₂ /In _{0.53} Ga _{0.47} As Metal-Oxide-Semiconductor Field-Effect Transistors. IEEE Electron Device Letters, 2016, , 1-1.	2.2	21
2	In _{0.53} Ga _{0.47} As FinFET and GAA-FET With Remote-Plasma Treatment. IEEE Electron Device Letters, 2018, 39, 339-342.	2.2	19
3	Screw-Dislocation-Driven Growth Mode in Two Dimensional GaSe on GaAs(001) Substrates Grown by Molecular Beam Epitaxy. Scientific Reports, 2019, 9, 17781.	1.6	17
4	Impact of interfacial misfit dislocation growth mode on highly lattice-mismatched In _x Ga _{1-x} Sb epilayer grown on GaAs substrate by metalorganic chemical vapor deposition. Applied Physics Letters, 2016, 109, .	1.5	14
5	Investigation of Mo/Ti/AlN/HfO ₂ High- k Metal Gate Stack for Low Power Consumption InGaAs NMOS Device Application. IEEE Electron Device Letters, 2017, 38, 552-555.	2.2	9
6	Pressure induced structural phase crossover of a GaSe epilayer grown under screw dislocation driven mode and its phase recovery. Scientific Reports, 2021, 11, 19887.	1.6	8
7	Methods for Extracting Flat Band Voltage in the InGaAs High Mobility Materials. IEEE Electron Device Letters, 2016, 37, 1100-1103.	2.2	7
8	Materials growth and band offset determination of Al ₂ O ₃ /In _{0.15} Ga _{0.85} Sb/GaSb/GaAs heterostructure grown by metalorganic chemical vapor deposition. Applied Physics Letters, 2017, 110, .	1.5	6
9	Molecular Beam Epitaxy of Two-Dimensional GaTe Nanostructures on GaAs(001) Substrates: Implication for Near-Infrared Photodetection. ACS Applied Nano Materials, 2021, 4, 8913-8921.	2.4	6
10	Growth of high-quality In _{0.28} Ga _{0.72} Sb/AlSb/GaSb/GaAs heterostructure by metalorganic chemical vapor deposition for single-channel Sb-based complementary metal-oxide-semiconductor applications. Applied Physics Express, 2017, 10, 075505.	1.1	5
11	Investigation of Multilayer TiNi Alloys as the Gate Metal for nMOS In _{0.53} Ga _{0.47} As. IEEE Transactions on Electron Devices, 2016, 63, 4714-4719.	1.6	4
12	Demonstrating antiphase domain boundary-free GaAs buffer layer on zero off-cut Si (0°) substrate for interfacial misfit dislocation GaSb film by metalorganic chemical vapor deposition. Materials Research Express, 2017, 4, 085901.	0.8	4
13	Study of the interface stability of the metal (Mo, Ni, Pd)/HfO ₂ /AlN/InGaAs MOS devices. AIP Advances, 2017, 7, 085208.	0.6	3
14	Nonlinear dependence of X-ray diffraction peak broadening in In _x Ga _{1-x} Sb epitaxial layers on GaAs substrates. Applied Physics Express, 2018, 11, 045503.	1.1	3
15	Entirely relaxed lattice-mismatched GaSb/GaAs/Si(001) heterostructure grown via metalorganic chemical vapor deposition. Applied Physics Express, 2018, 11, 051202.	1.1	2
16	Effect of Two-Step Metal Organic Chemical Vapor Deposition Growth on Quality, Diameter and Density of InAs Nanowires on Si (111) Substrate. Journal of Electronic Materials, 2018, 47, 1071-1079.	1.0	2
17	The effect of a Sb and Ga intermediate layer on the interfacial layer properties of epitaxial GaSb on GaAs grown by metalorganic chemical vapor deposition. Thin Solid Films, 2019, 669, 430-435.	0.8	2